



## Active

- L1: (59121) flash adj3 memory
- L2: (8878) \$3charg\$4 adj3 (bit-line or (bit adj line) or bitline)
- L4: (158) 1 same 2
- L6: (742) (precharg\$4 or pre-charge\$4 or charg\$4) adj3 (non-selected) or (non adj selected) adj2...
- L7: (34) 1 same 6
- L8: (281) (precharg\$4 or pre-charge\$4 or charg\$4) adj3 ((non-selected) or (non adj selected) adj2...
- L9: (11) 1 same 8
- L12: (8285) (charg\$4 or precharg\$4 or pre-charge\$4 or (pre adj charg\$4)) adj3 (bit-line or (bit a...
- L13: (67) (precharg\$4 or pre-charge\$4 or charg\$4) adj3 ((un-selected) or (unselected) adj2 (bit-l...
- L14: (26) 1 and 13
- L16: (41) 13 not 14
- L17: (276) 8 not 13
- L18: (87) 1 and 17
- L19: (22) charg\$4 adj3 ((non-selected) or (non adj selected) adj2 (bit-line or (bit adj line) o...
- L23: (26) precharg\$4 adj3 ((non-selected) or (non adj selected) adj2 (bit-line or (bit adj line...
- L24: (24) 23 not 19
- L30: (8285) (precharg\$4 or pre-charge\$4 or charg\$4) adj3 (bit-line or (bit adj line) or bitline)
- L31: (10904) 365/185\$3
- L32: (1266) 30 and 31
- L33: (643) 365/185.25
- L34: (965) 365/185.28
- L35: (2200) 365/185.33
- L36: (249) 30 and 33
- L37: (108) 30 and 34
- L38: (177) 30 and 35
- L39: (27) (precharg\$4 or pre-charge\$4 or charg\$4) adj3 (dataline or data-line or datat adj line)
- L40: (561) (precharg\$4 or pre-charge\$4 or charg\$4) adj3 (digitline or digit-line or digit adj line)
- L42: (1) 40 and 34
- L43: (1) 40 and 35
- L41: (8) 40 and 33
- L44: (63) 40 and 31
- L45: (1266) 30 and 31
- L46: (114) 6 and 45
- L47: (20) (chang\$4 near2 you).in.

## Failed

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DBs: USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM; TDB ☒ Plurals

Default operator:  ☒ Highlight all hit terms initially

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	U	1	2	3	Document ID#	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cld	Inventor	S	C	P
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6028788 A	20000222	21	Flash memory device	365/185.11	365/185.17; 365/185.33		Choi, Jeong-hyuk et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6195297 B1	20010227	13	Semiconductor memory device	365/189.11	365/185.25; 365/203		Sano, Yuuichi	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6480419 B2	20021112	16	having pull-down function for non-Bit line setup and discharge circuit for programming non-volatile me	365/185.18	365/185.25; 365/203		Lee, Yeong-Tack	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6650666 B2	20031118	13	Nonvolatile semiconductor memory with a programming ooper	365/185.12	365/185.05		Jeong, Jae-Yong et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

Hits Details HTML

Ready